IR HiRel
An Infineon Technologies Company

IRF360

REPETITIVE AVALANCHE AND dv/dt RATED HEXFET®TRANSISTORS THRU-HOLE -TO-3 (TO-204AE)

400V, N-CHANNEL

Product Summary

Part Number	BV_{DSS}	RDS(on)	I_D
IRF360	400V	0.20Ω	25A


TO-3 (TO-204AE)

Description

HEXFET® MOSFET technology is the key to IR Hirel advanced line of power MOSFET transistors. The efficient geometry and unique processing of this latest “State of the Art” design achieves: very low on-state resistance combined with high trans conductance; superior reverse energy and diode recovery dv/dt capability.
The HEXFET transistors also feature all of the well established advantages of MOSFETs such as voltage control, very fast switching and temperature stability of the electrical parameters.
They are well suited for applications such as switching power supplies, motor controls, inverters, choppers, audio amplifiers and high energy pulse circuits.

Features

- Repetitive Avalanche Ratings
- Dynamic dv/dt Rating
- Hermetically Sealed
- Simple Drive Requirements

Absolute Maximum Ratings

Symbol	Parameter	Value	Units
I_{D1} @ V_{GS} = 10V, T_C = 25°C	Continuous Drain Current	25	A
I_{D2} @ V_{GS} = 10V, T_C = 100°C	Continuous Drain Current	16	
I_{DM} @ T_C = 25°C	Pulsed Drain Current ①	100	
P_D @ T_C = 25°C	Maximum Power Dissipation	300	W
	Linear Derating Factor	2.4	W/°C
V_{GS}	Gate-to-Source Voltage	± 20	V
E_{AS}	Single Pulse Avalanche Energy ②	980	mJ
I_{AR}	Avalanche Current ①	25	A
E_{AR}	Repetitive Avalanche Energy ①	30	mJ
dv/dt	Peak Diode Recovery ③	4.0	V/ns
T_J T_{STG}	Operating Junction and Storage Temperature Range	-55 to + 150	°C
	Lead Temperature	300 (0.063 in. (1.6mm) from case for 10s)	
	Weight	11.5 (Typical)	g

For footnotes refer to the page 2.

Electrical Characteristics @ Tj = 25°C (Unless Otherwise Specified)

Symbol	Parameter	Min.	Typ.	Max.	Units	Test Conditions
BV_{DSS}	Drain-to-Source Breakdown Voltage	400	—	—	V	V_{GS} = 0V, I_D = 1.0mA
$\Delta BV_{DSS}/\Delta T_J$	Breakdown Voltage Temp. Coefficient	—	0.46	—	V/°C	Reference to 25°C, I_D = 1.0mA
$R_{DS(on)}$	Static Drain-to-Source On-Resistance	—	—	0.20	Ω	V_{GS} = 10V, I_{D2} = 16A ④
		—	—	0.23		V_{GS} = 10V, I_{D2} = 25A ④
$V_{GS(th)}$	Gate Threshold Voltage	2.0	—	4.0	V	$V_{DS} = V_{GS}$, I_D = 250µA
I_{DSS}	Zero Gate Voltage Drain Current	—	—	25	µA	V_{DS} = 320V, V_{GS} = 0V
		—	—	250		V_{DS} = 320V, V_{GS} = 0V, T_J = 125°C
I_{GSS}	Gate-to-Source Leakage Forward	—	—	100	nA	V_{GS} = 20V
	Gate-to-Source Leakage Reverse	—	—	-100		V_{GS} = -20V
Q_G	Total Gate Charge	96	—	210	nC	I_{D1} = 25A
Q_{GS}	Gate-to-Source Charge	11	—	28		V_{DS} = 200V
Q_{GD}	Gate-to-Drain ('Miller') Charge	53	—	120		V_{GS} = 10V
$t_{d(on)}$	Turn-On Delay Time	—	—	33	ns	V_{DD} = 200V
tr	Rise Time	—	—	140		I_{D1} = 25A
$t_{d(off)}$	Turn-Off Delay Time	—	—	120		R_G = 2.35Ω
t_f	Fall Time	—	—	99		V_{GS} = 10V
$L_S + L_D$	Total Inductance	—	6.1	—	nH	Measured from Drain lead (6mm / 0.25 in from package) to Source lead (6mm/ 0.25 in from package)
C_{iss}	Input Capacitance	—	4200	—	pF	V_{GS} = 0V
C_{oss}	Output Capacitance	—	900	—		V_{DS} = 25V
C_{rss}	Reverse Transfer Capacitance	—	400	—		f = 1.0MHz

Source-Drain Diode Ratings and Characteristics

Symbol	Parameter	Min.	Typ.	Max.	Units	Test Conditions
I_S	Continuous Source Current (Body Diode)	—	—	25	A	
I_{SM}	Pulsed Source Current (Body Diode) ①	—	—	100		
V_{SD}	Diode Forward Voltage	—	—	1.8	V	T_J = 25°C, I_S = 25A, V_{GS} = 0V④
t_{rr}	Reverse Recovery Time	—	—	1000	ns	T_J = 25°C, I_F = 25A, $V_{DD} \leq$ 50V
Q_{rr}	Reverse Recovery Charge	—	—	16	µC	di/dt = 100A/µs ④
t_{on}	Forward Turn-On Time	Intrinsic turn-on time is negligible (turn-on is dominated by L_S+L_D)				

Thermal Resistance

Symbol	Parameter	Min.	Typ.	Max.	Units
$R_{\theta JC}$	Junction-to-Case	—	—	0.42	°C/W
$R_{\theta JA}$	Junction-to-Ambient (Typical socket mount)	—	—	30	

Footnotes:

① Repetitive Rating; Pulse width limited by maximum junction temperature.

② V_{DD} = 50V, starting T_J = 25°C, L= 3.14mH, Peak I_L = 25A, V_{GS} = 10V.

③ $I_{SD} \leq$ 25A, di/dt $\leq$ 170A/µs, $V_{DD} \leq$ 400V, $T_J \leq$ 150°C.Suggested R_G = 2.35Ω

④ Pulse width $\leq$ 300 µs; Duty Cycle $\leq$ 2%

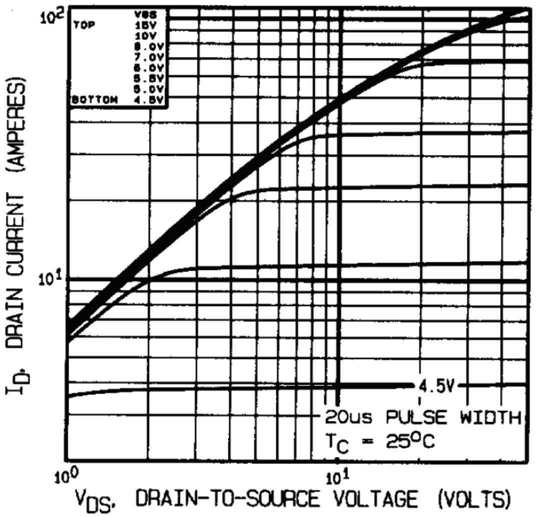


Fig 1. Typical Output Characteristics

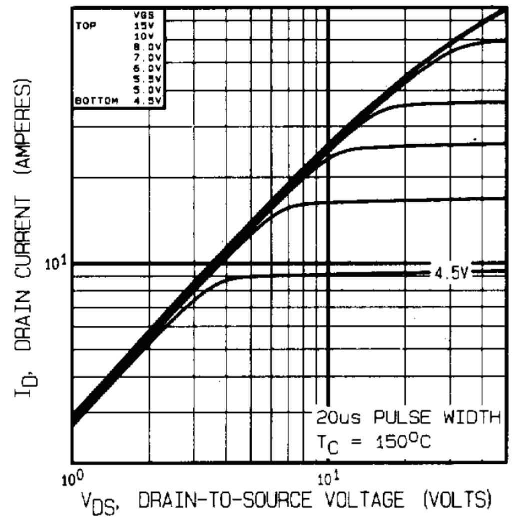


Fig 2. Typical Output Characteristics

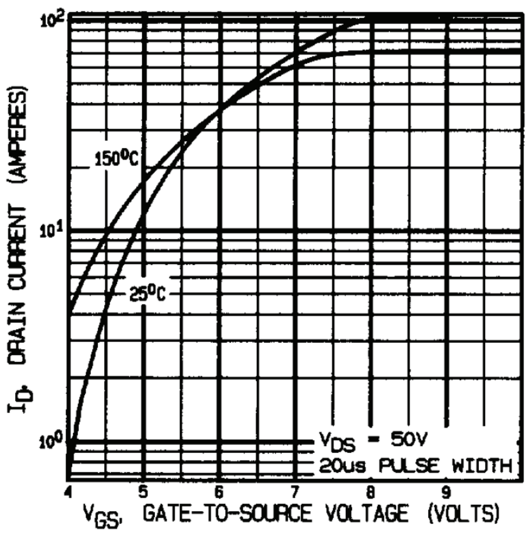


Fig 3. Typical Transfer Characteristics

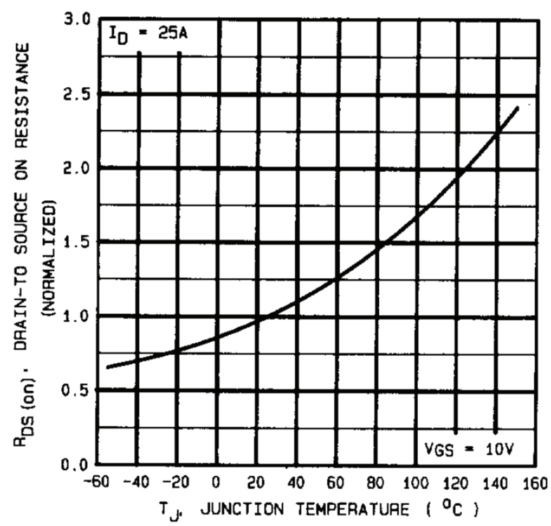


Fig 4. Normalized On-Resistance Vs. Temperature

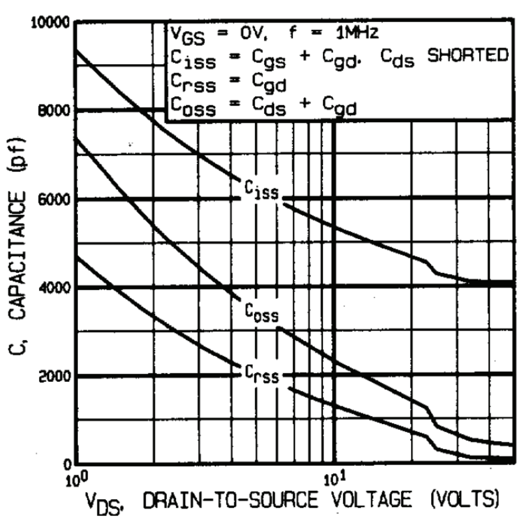


Fig 5. Typical Capacitance Vs. Drain-to-Source Voltage

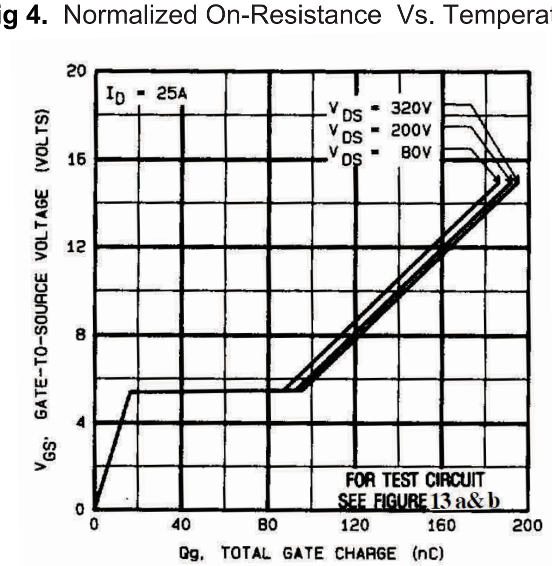


Fig 6. Typical Gate Charge Vs. Gate-to-Source Voltage

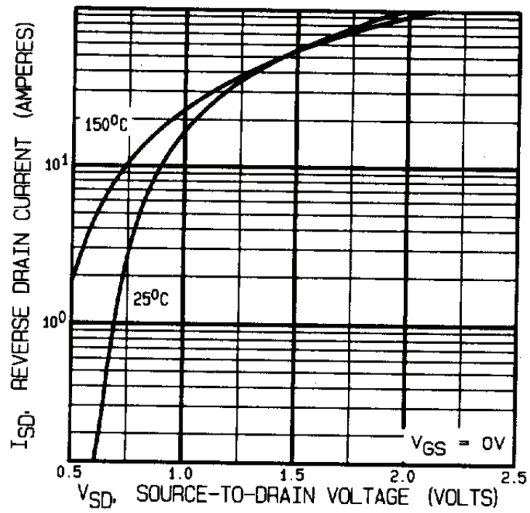


Fig 7. Typical Source-Drain Diode Forward Voltage

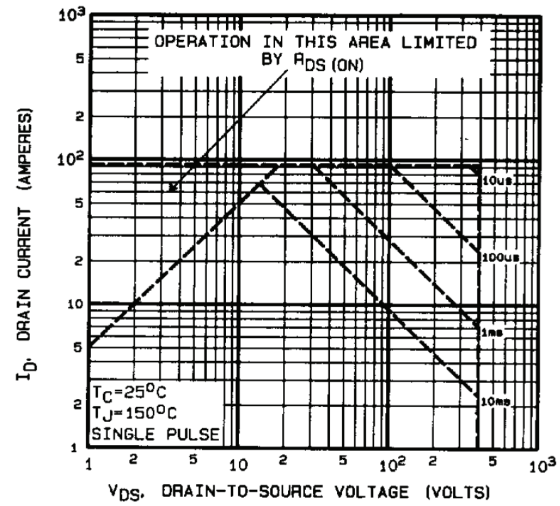


Fig 8. Maximum Safe Operating Area

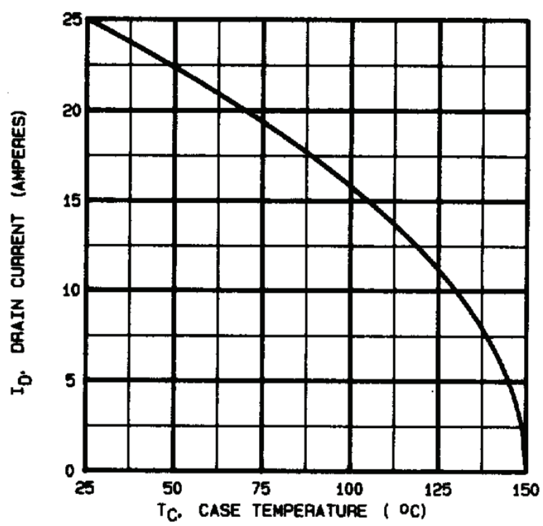


Fig 9. Maximum Drain Current Vs. Case Temperature

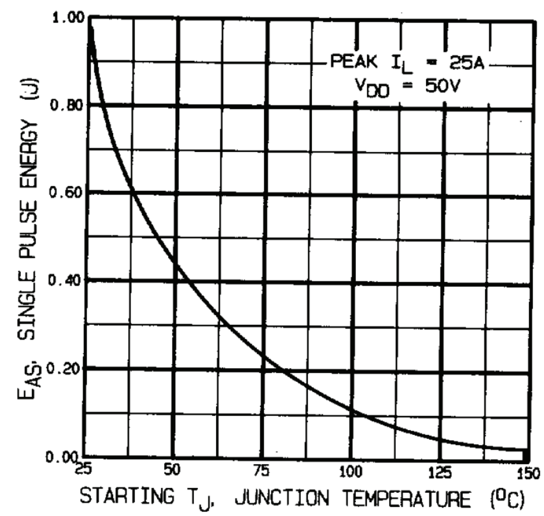


Fig 10. Maximum Avalanche Energy
Vs. Drain Current

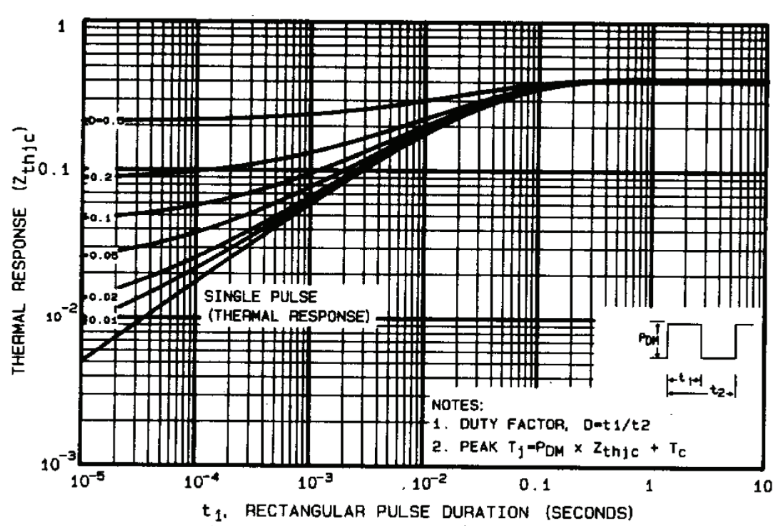


Fig 11. Maximum Effective Transient Thermal Impedance, Junction-to-Case

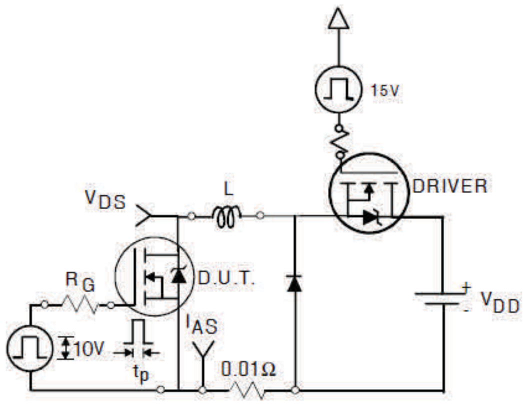


Fig 12a. Unclamped Inductive Test Circuit

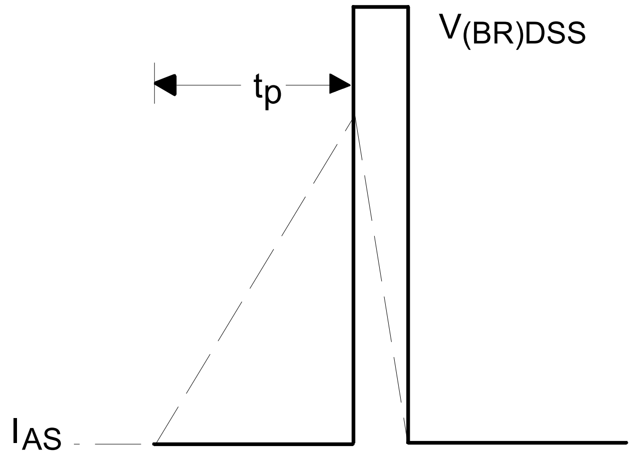


Fig 12b. Unclamped Inductive Waveforms

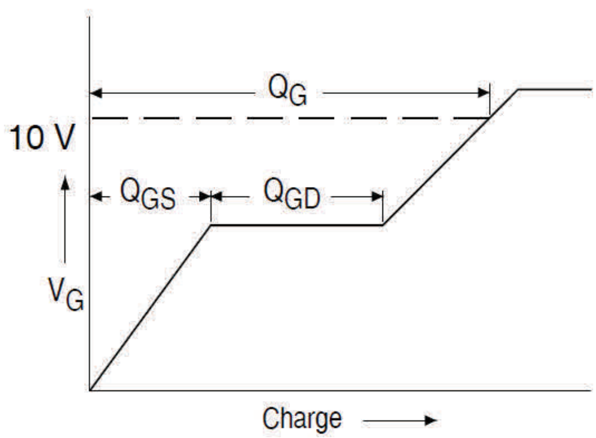


Fig 13a. Gate Charge Waveform

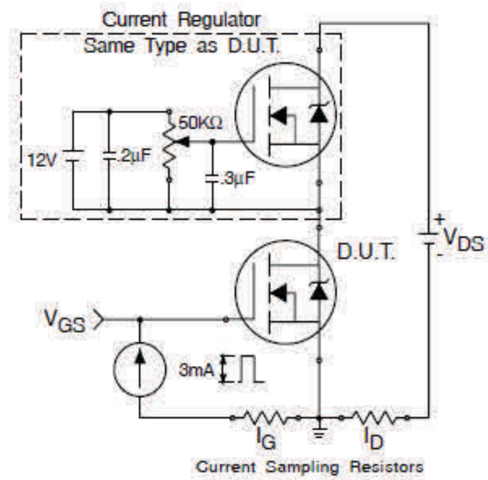


Fig 13b. Gate Charge Test Circuit

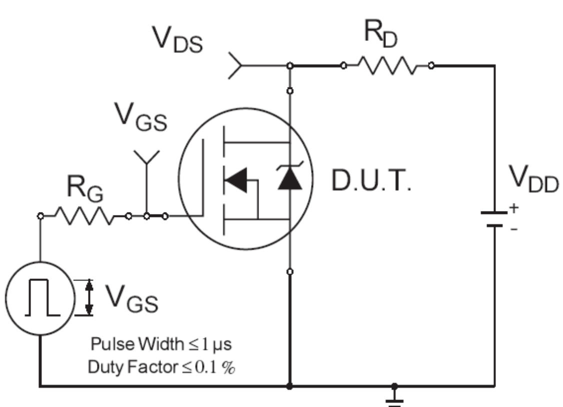


Fig 14a. Switching Time Test Circuit

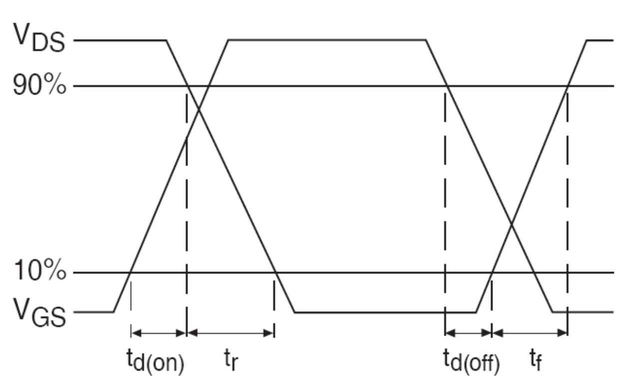
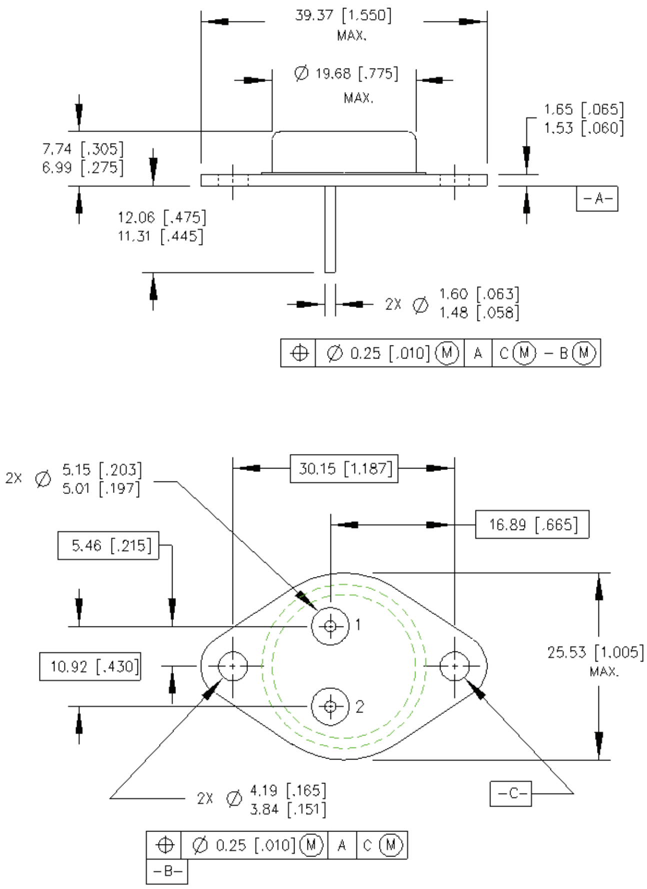


Fig 14b. Switching Time Waveforms

Case Outline and Dimensions - TO-204AE (Modified TO-3)



PIN ASSIGNMENTS

HEXFET	SCHOTTKY	IGBT
1 - SOURCE	1 - ANODE 1	1 - GATE
2 - GATE	2 - ANODE 2	2 - EMITTER
3 - DRAIN (CASE)	3 - COMMON CATHOD (CASE)	3 - COLLECTOR (CASE)

NOTES:
1. DIMENSIONING & TOLERANCING PER ANSI Y14.5M -1982.
2. CONTROLLING DIMENSION : INCH.
3. DIMENSIONS ARE SHOWN IN MILLIMETERS [INCHES].
4. OUTLINE CONFORMS TO JEDEC OUTLINE TO -204-AE.

IOR HiRel
An Infineon Technologies Company
www.infineon.com/irhirel

Infineon Technologies Service Center: USA Tel: +1 (866) 951-9519 and International Tel: +49 89 234 65555
Leominster, Massachusetts 01453, USA Tel: +1 (978) 534-5776
San Jose, California 95134, USA Tel: +1 (408) 434-5000

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